

PATENT 5500-36100/TT2823

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re Application of:

Gardner, et al.

Serial No. 09/207,972

Filed: December 9, 1998

For:

ULTRATHIN HIGH-K GATE

DIELECTRIC WITH FAVORABLE INTERFACE PROPERTIES FOR IMPROVED SEMICONDUCTOR

DEVICE PERFORMANCE

Group Art Unit: 2815

Examiner: Warren, M.

AUG 1 5 2001

Technology Center 2600

Atty. Dkt. No. 5500-36100

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on the date indicated below:

August 9, 2001

Kevin L. Daffer

AMENDMENT; RESPONSE TO OFFICE ACTION MAILED MAY 9, 2001

Assistant Commissioner for Patents Washington, D.C. 20231

Dear Sir/Madam:

nt Commissioner for Patents
Igton, D.C. 20231

r/Madam:

This paper is submitted in response to the Office Action of May 9, 2001 to further of the condition for allowance. highlight why the application is in condition for allowance.

Please amend the case as listed below.

In the Claims:

Please add the following claims:

30. (Added) The device as recited in claim 16, wherein said high-K dielectric has a low-trapdensity.